RECOMMEND
YJG2D7G06A

ɣ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250εA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V			1	εA
Gate-Body Leakage Current	I_{GSS}	V_{GS}= 20V, V_{DS}=0V			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250εA	1.2	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D=20A		2.1	2.5	mq
		V_{GS}= 4.5V, I_D=15A		2.7	3.4	
Diode Forward Voltage	V_{SD}	I_S=20A,V_{GS}=0V			1.2	V
Maximum Body-Diode Continuous Current	I_S				95	

Typical Performance Characteristics

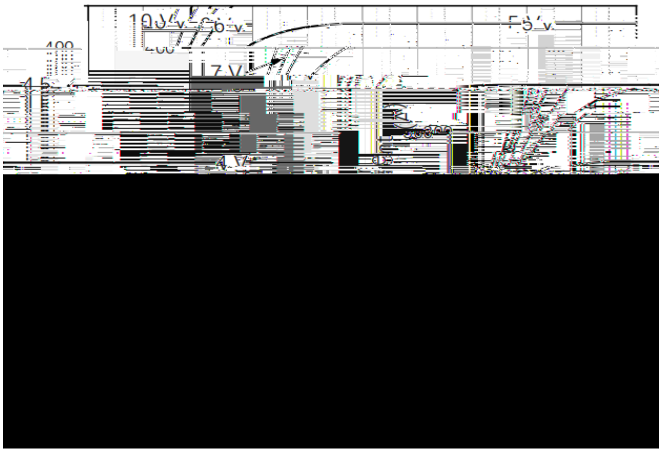

Figure1. Output Characteristics

Figure2. Transfer Characteristics

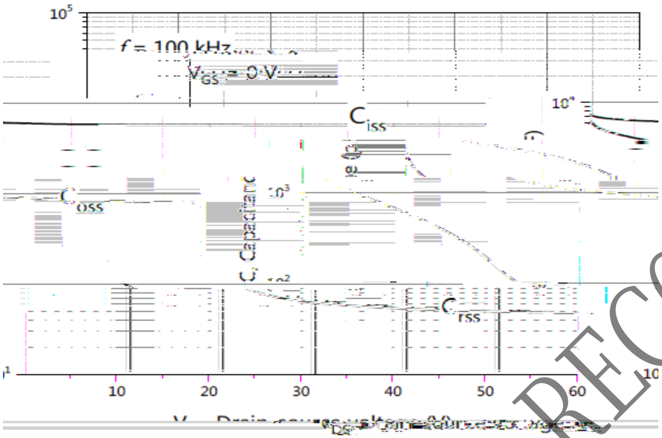

Figure3. Capacitance Characteristics

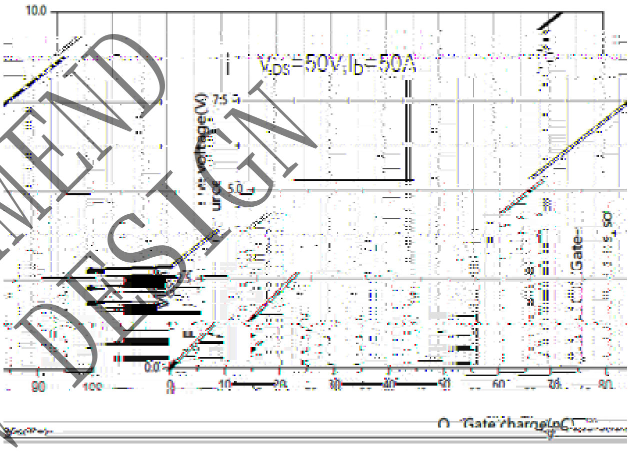

Figure4. Gate Charge

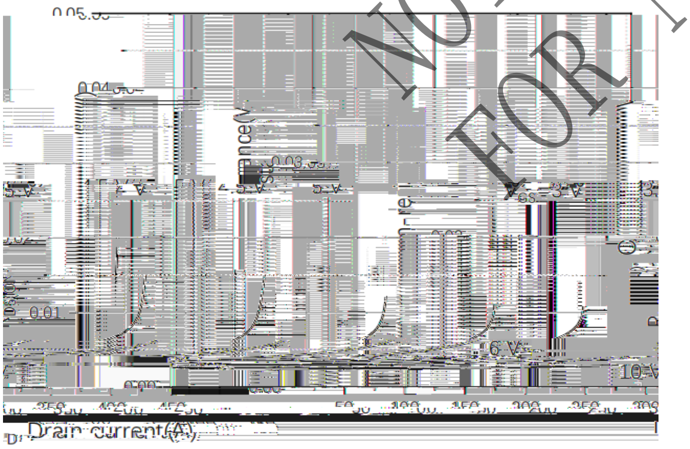

Figure5. Drain-Source on Resistance

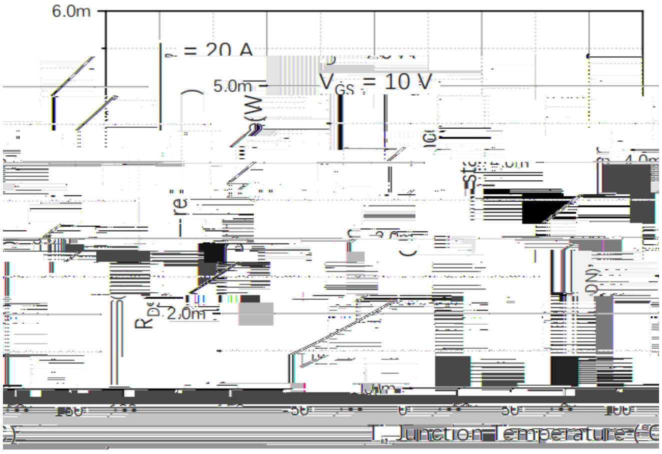

Figure6. Drain-Source on Resistance

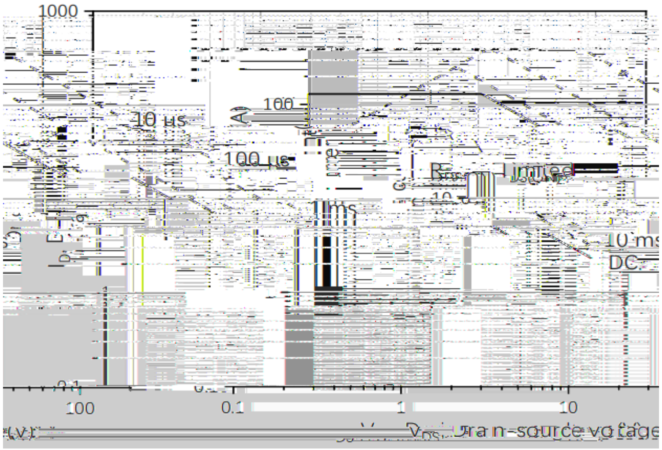

Figure7. Safe Operation Area

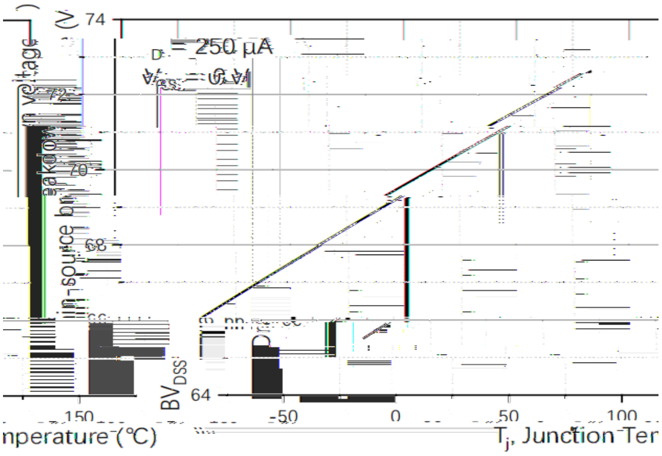

Figure8. Drain-source breakdown voltage

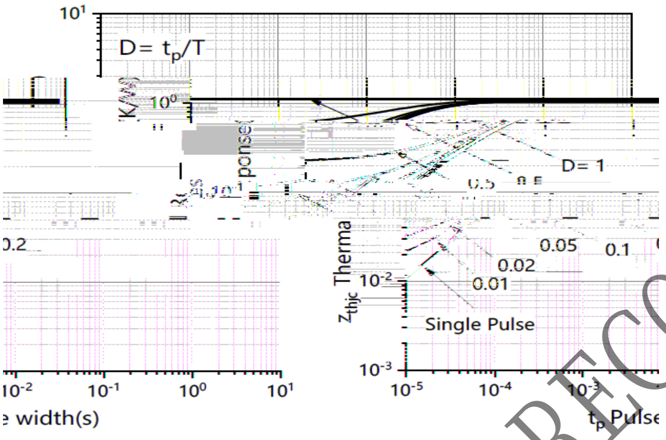

Figure 9.Transient thermal impedance

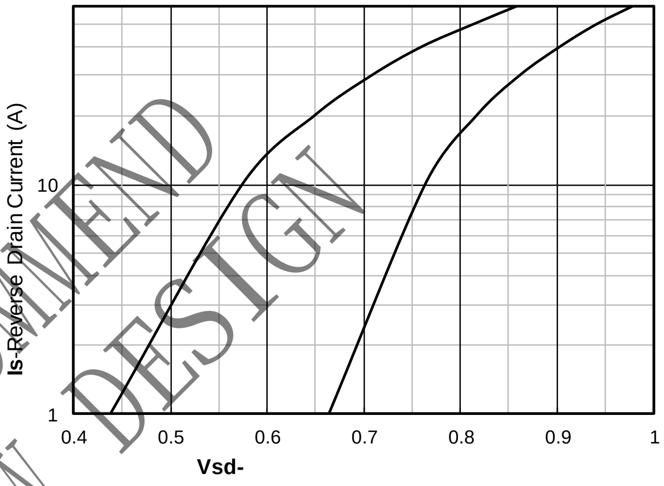

Figure 10. Forward characteristics of reverse diode

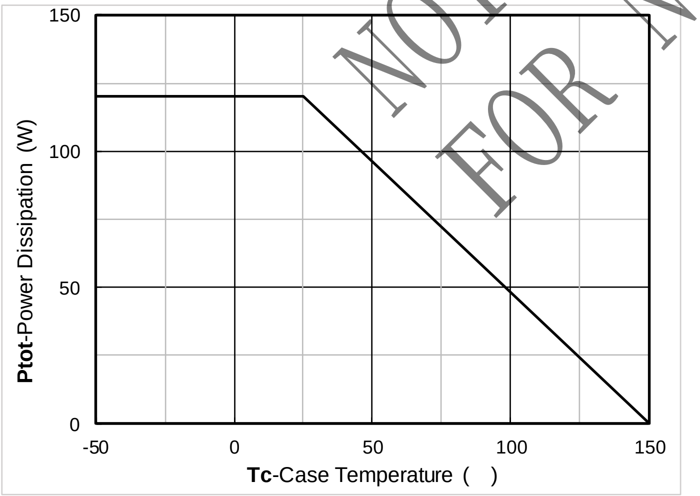

Figure 11. Power dissipation